

# isc N-Channel MOSFET Transistor

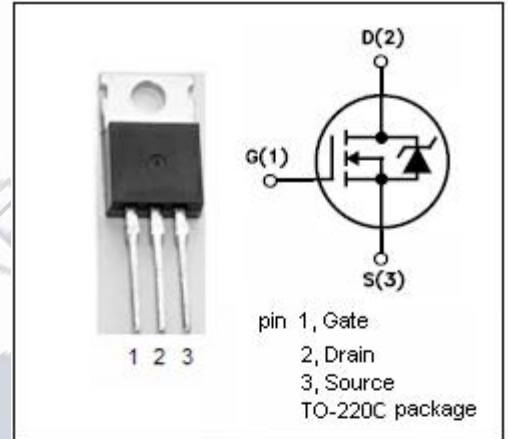
# IRFZ24N

## FEATURES

- Drain Source Voltage-  
:  $V_{DSS} = 55V$ (Min)
- Static Drain-Source On-Resistance  
:  $R_{DS(on)} = 157m\Omega$  (Max)
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## DESCRIPTION

- Intended for use in switched mode power supplies  
And general purpose switching applications

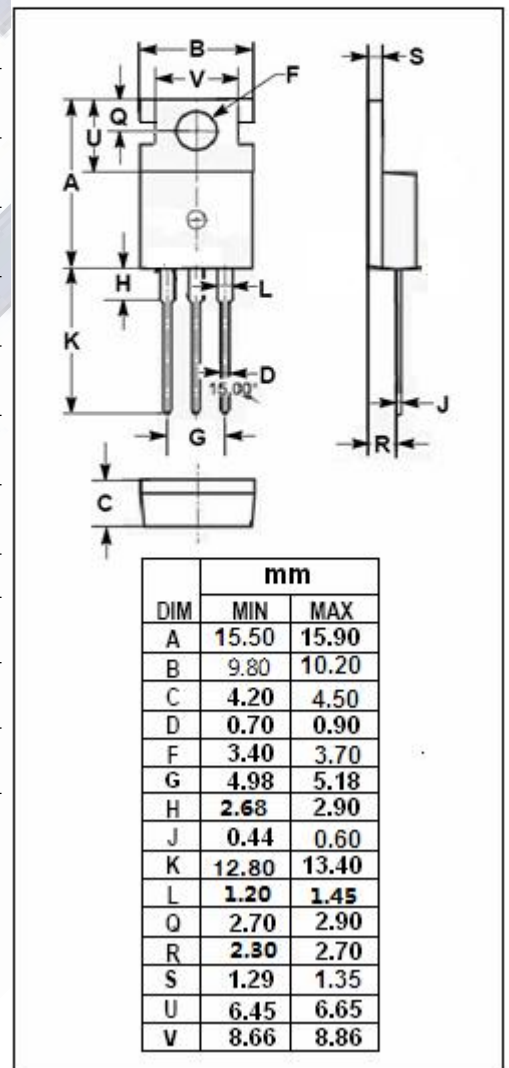


## ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage	55	V
$V_{GS}$	Gate-Source Voltage-Continuous	$\pm 20$	V
$I_D$	Drain Current-Continuous	17	A
$P_D$	Total Dissipation @ $T_c=25^\circ C$	45	W
$T_J$	Max. Operating Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature	-55~150	$^\circ C$

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	3.3	$^\circ C/W$
$R_{th j-a}$	Thermal Resistance, Junction to Ambient	60	$^\circ C/W$



**isc N-Channel MOSFET Transistor****IRFZ24N****ELECTRICAL CHARACTERISTICS****T<sub>C</sub>=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> = 0.25mA	55		V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> = 1mA	2	4	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> = 10A		157	mΩ
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±10V; V <sub>DS</sub> = 0		±1	μA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 55V; V <sub>GS</sub> = 0		10	μA
V <sub>SD</sub>	Forward On-Voltage	I <sub>S</sub> =10.7A; V <sub>GS</sub> = 0		1.2	V